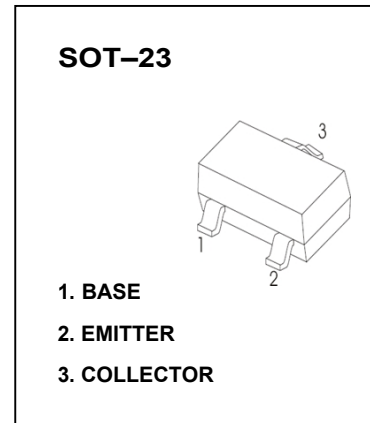


SOT-23 Plastic-Encapsulate Transistors

2SC4155A Transistor Silicon NPN Epitaxial Type

FEATURE

- Small collector to emitter saturation voltage.
VCE(sat)=0.3V max
- Excellent linearity of DC forward gain.
- Super mini package for easy mounting



MAXIMUM RATINGS (Ta=25°C)

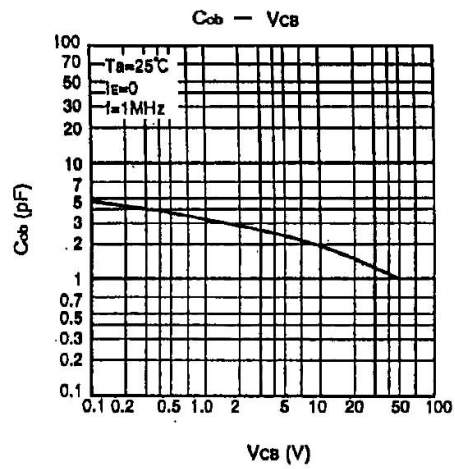
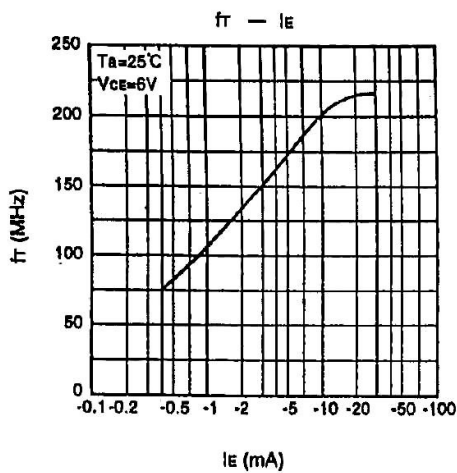
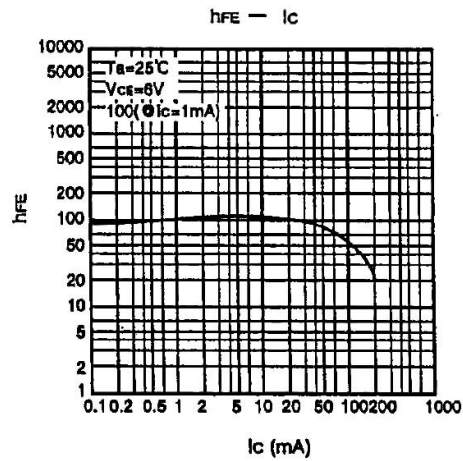
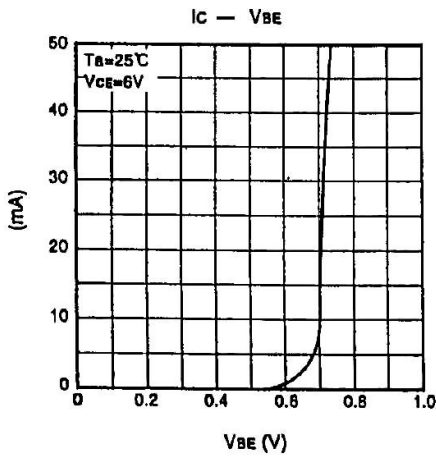
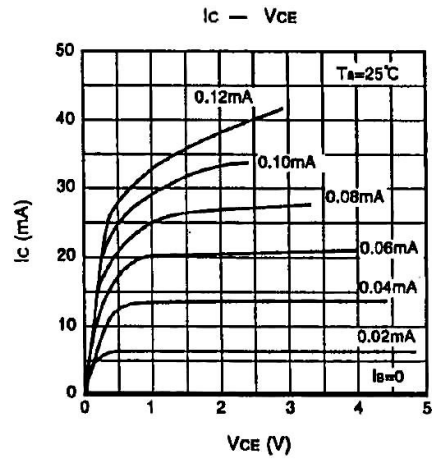
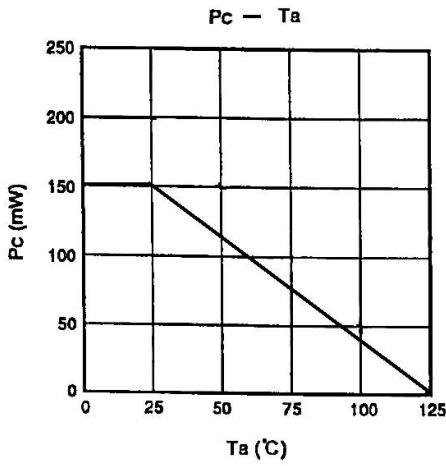
Symbol	Parameter	Ratings	Unit
V _{CBO}	Collector to Base voltage	50	V
V _{CEO}	Collector to Emitter voltage	50	V
V _{EBO}	Emitter to Base voltage	6	V
I _O	Collector current	200	mA
P _c	Collector dissipation	200	mW
T _j	Junction temperature	+150	°C
T _{stg}	Storage temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

Parameter	Symbol	Test conditions	Limits			Unit
			Min	Typ	Max	
C to E break down voltage	V(BR) _{CEO}	IC=100 μ A, RBE=∞	50	—	—	V
Collector cut off current	ICBO	VCE=50V, IE=0	—	—	0.1	μ A
Emitter cut off current	IEBO	VEB=4V, IC=0	—	—	0.1	μ A
DC forward current gain	hFE	VCE=6V, IC=1mA	120	(※)	820	—
DC forward current gain	hFE	VCE=6V, IC=0.1mA	70	—	—	—
C to E Saturation Voltage	VCE(sat)	IC=100mA, IB=10mA	—	—	0.3	V
Gain bandwidth product	fT	VCE=6V, IE=-10mA	—	200	—	MHz
Collector output capacitance	Cob	VCE=6V, IE=0, f=1MHz	—	4	—	pF
Noise Figure	NF	VCE=6V, IE=-0.1mA, f=1kHz, RG=2kΩ	—	—	15	dB

h _{FE} Classifications Symbol	Q	R	S	T
h _{FE} Range	120~270	180~390	270~560	390~820
Marking	HQH	HRH	HHS	HHT

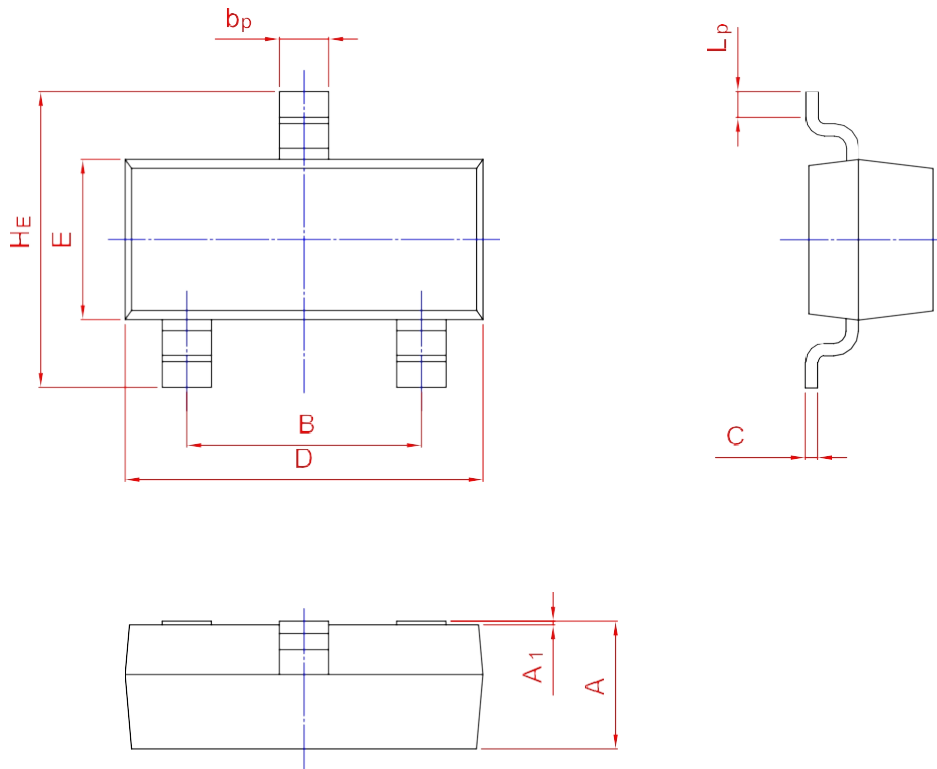
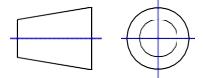
Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b _p	C	D	E	H _E	A ₁	L _p
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20